CPH6355

Power MOSFET -30V, $169m\Omega$, -3A, Single P-Channel



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Features

- Low ON-Resistance
- 4V Drive
- Pb-Free, Halogen Free and RoHS Compliance

VDSS	R _{DS} (on) Max	ID Max
	169mΩ@ -10V	
-30V	276mΩ@ -4.5V	-3A
	313mΩ@ –4V	

Specifications

Absolute Maximum Ratings at Ta = 25°C

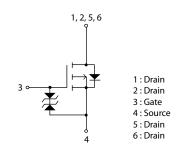
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	-30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	-3	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	-12	А
Power Dissipation When mounted on ceramic substrate (1500mm² × 0.8mm)	PD	1.6	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

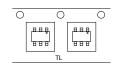
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1500mm ² × 0.8mm)	R _{θJA}	78.1	°C/W

Electrical Connection P-Channel



Packing Type: TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*} Machine Model

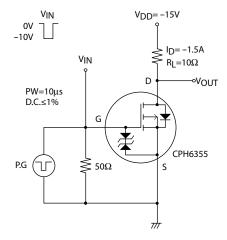
CPH6355

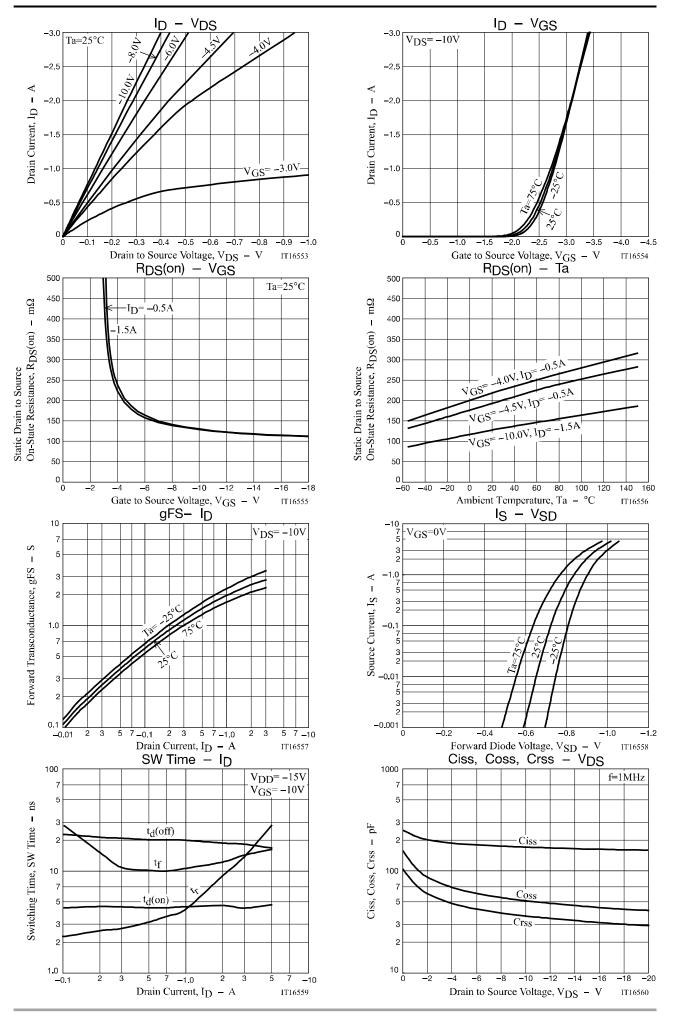
Electrical Characteristics at Ta = 25°C

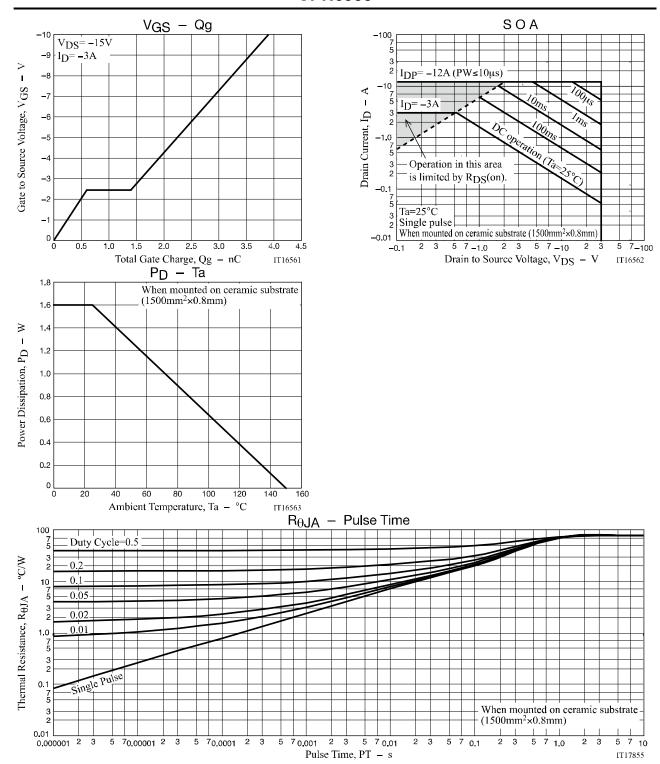
Parameter	Symbol	O contitions	Value			11.2
		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-30V, V _{GS} =0V			-1	μА
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-1.5A		2.3		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =-1.5A, V _{GS} =-10V		130	169	mΩ
	R _{DS} (on)2	I _D =-0.5A, V _{GS} =-4.5V		197	276	mΩ
	R _{DS} (on)3	I _D =-0.5A, V _{GS} =-4V		223	313	mΩ
Input Capacitance	Ciss			172		pF
Output Capacitance	Coss	V _{DS} =–10V, f=1MHz		51		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t _d (on)			4.6		ns
Rise Time	t _r			6.6		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		19.4		ns
Fall Time	t _f			11.4		ns
Total Gate Charge	Qg			3.9		nC
Gate to Source Charge	Qgs	V _{DS} =-15V, V _{GS} =-10V, I _D =-3A		0.6		nC
Gate to Drain "Miller" Charge	Qgd	7		8.0		nC
Forward Diode Voltage	V _{SD}	I _S =-3A, V _{GS} =0V		-0.95	-1.5	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







Package Dimensions

CPH6355-TL-H / CPH6355-TL-W

CPH₆

CASE 318BD ISSUE O

Unit: mm

1: Drain

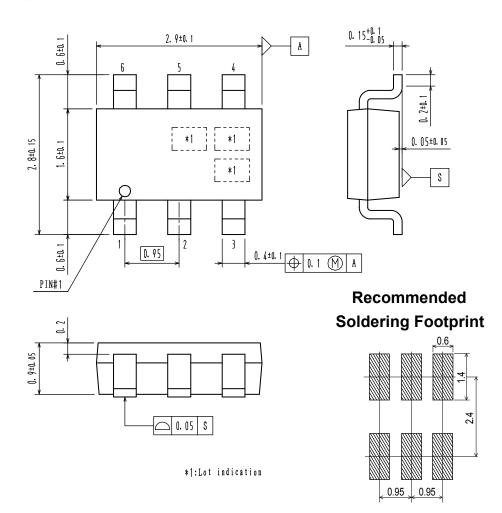
2: Drain

3: Gate

4 : Source

5: Drain

6: Drain



ORDERING INFORMATION

Device	Package	Shipping	Note
CPH6355-TL-H	CPH6, SC-74	3,000 pcs. / Tape & Reel	Pb-Free and
CPH6355-TL-W	355-TL-W SOT-26, SOT-457	5,000 pcs. / Tape & Reel	Halogen Free

Note on usage: Since the CPH6355 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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